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NEW APPLICATION TRANSMITTAL FILING
UNDER 37 CFR§1.53(b)

Transmitted herewith for filing is the patent application of:

Inventor(s): Yan Rozenzon et al.

For: TEMPERATURE CONTROLLED WINDOW WITH A FLUID SUPPLY SYSTEM

Enclosed are:

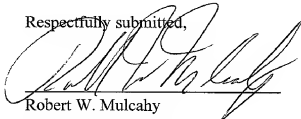
- ☒ Specification, Claims and Abstract Totaling 25 Pages
- ☒ Nine (9) Sheet(s) of **FORMAL** Drawings

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UNITED STATES PATENT APPLICATION FOR:

TEMPERATURE CONTROLLED WINDOW
WITH A FLUID SUPPLY SYSTEM

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Certification Under 37 CFR 1.10

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**TEMPERATURE CONTROLLED WINDOW
WITH A FLUID SUPPLY SYSTEM****BACKGROUND OF THE INVENTION****5 Field of the Invention**

The present invention relates to an apparatus and method for controlling the temperature of a surface in a processing chamber. More specifically, the invention relates to methods and apparatus for controlling the temperature of an energy transparent window or electrode of a processing chamber.

10 Background of the Related Art

Many processes for fabricating integrated circuits and other electronic devices, such as etching, chemical vapor deposition, and physical vapor deposition, are plasma-enhanced or plasma-assisted. These processes employ process gases which excited to a plasma state within a vacuum chamber. As one example, plasma etching (typically referred to as "dry" etching) has become a well accepted process in semiconductor manufacturing. The etching process removes patterned material from the substrate surface located in a substrate processing system.

Gases are the primary dry etch medium, and plasma energy is used to drive the reaction. The plasma is created by applying an electrical field to a gas or combination of gases. Inside the chamber, the substrate to be processed is placed on a negatively charged cathode. Positively charged ions from the plasma are attracted and accelerated toward the cathode's negative charge, and the ions impact the substrate surface. The ability to attract ions in a direction normal to the substrate surface allows manufacturers of integrated circuits and other electronic devices to achieve high quality, vertical etching profiles.

The plasma etch process occurs in two ways, either separately or in combination, depending on the material to be etched and the etch chemistry used: (1) chemically reactive ions and free radicals formed in the plasma strike the substrate surface where they react with the surface material and form volatile compounds which can be exhausted from the system; and (2) the ions may be attracted to the substrate surface and strike the substrate surface with sufficient impact energy to break the chemical bonds in the film, physically dislodging or "sputtering" material from the substrate surface.

In a plasma processing chamber, radio frequency (RF) is used to generate and maintain

a plasma within the processing chamber. It is often necessary to control temperatures of surfaces within the process chamber. This is particularly true in the case of a reactor chamber having a window electrode which acts as either an electrode or a window for admitting RF power from an inductive antenna therethrough. For example, the lid temperature tends to rise during plasma generation, due to heat absorption from the plasma and RF energy being coupled into the plasma. The plasma may cause the chamber components, such as the electrode or window, to approach temperatures of 660°C and higher. The etch rate and etch selectivity can change as the temperature in the chamber changes. For example, the etch rate of oxides can decrease due to an increase in chamber temperature until eventually the etching may stop.

In addition, some cases where the window/electrode is a semiconducting material, it may be necessary to control the temperature of the window/electrode within a particular temperature range to obtain the proper electrical properties of the window. The application of RF power to generate and maintain the plasma leads to heating of the surfaces within the chamber, including windows or electrodes or for combination window/electrodes.

Prior efforts to effectuate temperature control of chamber components, such as windows and electrodes made of dielectric, non-metallic or semiconductive materials, have centered around indirect cooling which relies on thermal conduction of heat from the chamber components to a heat sink such as a cooled metallic body or cooling channels formed in the antennae or coils themselves. Attempts to provide temperature control in a processing chamber are shown in United States Patent Nos. 5,863,376 and 5,074,456. However, these attempts to achieve temperature control have failed to directly control the temperature of a dielectric, non-metallic or semiconductive window or electrode. As a result, only indirect cooling has been achieved. Moreover, such prior attempts have caused complications and interference when overhead coils or antennas have been called for in a plasma chamber. Obviously, cooling apparatus compete for the same space or area as the coils or antenna or the cooling apparatus must be combined with the coils or antenna, limiting the optimization of either design.

Therefore, there remains a need for a method and apparatus which directly controls the temperature of a dielectric, non-metallic or semiconductive window or electrode. A further need remains to accomplish the foregoing with coil based chamber designs.

Summary of the Invention

The present invention provides a method and apparatus for controlling the temperature of chamber components including ceramic, dielectric ceramic, and other non-metallic chamber components. One example of a temperature controlled chamber component of the invention includes an energy transparent window or electrode that allows efficient coupling of RF electromagnetic energy or microwave energy into the chamber. A fluid supply system delivers a fluid to a feedthrough and into a channel formed in the window or electrode. In one embodiment, a feedthrough mounts the window to a retaining ring and provides a conduit through which a fluid can be inlet and outlet from the fluid channel.

In one aspect, a window comprising a first and a second plate is provided. The plates define a channel therebetween and include one or more inlet/outlets through which fluids flow in and out of the channel. The channel may be formed in one or partially in both plates so that when the plates are bonded together they form the channel. The window is preferably made of a dielectric, non-metallic or semiconductive material, such as a ceramic, silicon, polysilicon and the like.

In another aspect, the invention provides a substrate processing system having a processing chamber, a chamber cover including a retaining ring and a window having a temperature control passageway disposed at least partially internal to the window and a fluid inlet and an outlet fluidly connected to the lid passageway.

Another aspect of the invention provides an apparatus for mounting a window on a chamber and providing a fluid onto the window. A retaining ring is provided to mount the window and support the window on the chamber. The retaining ring preferably includes one or more feedthrough channels in which a feedthrough can be disposed to secure the window to the retaining ring and deliver fluids into the window. The feedthrough is disposed through the retaining ring and secured thereto on one end through a threaded connection. The other end of the feedthrough is received in a feedthrough pocket formed in the window. The feedthrough is retained in the feedthrough pocket using an o-ring.

The invention also provides methods to control the temperature of a lid by delivering a fluid through a fluid inlet to a fluid passageway in the lid which is at least partially internal to the lid, and flowing the fluid through the fluid passageway. The temperature of the fluid is preferably controlled and monitored to enable accurate temperature control of the chamber

component.

Brief Description of the Drawings

So that the manner in which the above recited features, advantages and objects of the present invention are attained and can be understood in detail, a more particular description of the invention, briefly summarized above, may be had by reference to the embodiments thereof which are illustrated in the appended drawings.

It is to be noted, however, that the appended drawings illustrate only typical embodiments of this invention and are therefore not to be considered limiting of its scope, for the invention may admit to other equally effective embodiments.

Figure 1 is a cross section of an etch chamber of the invention.

Figure 1a is a cross section of an etch chamber of the invention having a flat coil.

Figure 2 is a substantially top perspective view of a coil array of an embodiment of the invention disposed on a lid assembly.

Figure 3 is a substantially top perspective view of one coil in the array shown in Figure 2.

Figure 4 is a cross sectional view of an energy transparent window of the invention.

Figure 5 is a bottom view of a top plate illustrating one channel pattern.

Figure 6 is a top view of a bottom plate illustrating one channel pattern.

Figure 7 is a bottom view of a top plate illustrating another channel pattern.

Figure 8 is a partial cross sectional view of a lid assembly showing the retaining ring, energy transparent window and a feedthrough.

Figure 9 is a cross sectional view of another embodiment of the invention illustrating an inductively coupled type chamber.

Figure 10 is a cross sectional view of another embodiment of the invention illustrating an inductively coupled type chamber.

Figure 11 is a cross sectional view of another embodiment of the invention illustrating a capacitively coupled type chamber.

Detailed Description of a Preferred Embodiment

The present invention provides a temperature controlled chamber component, such as a

ceramic, dielectric or semiconductive energy transparent window and/or electrode, particularly a chamber roof or lid electrode, for use in a substrate processing system. The invention also provides methods for controlling the temperature of chamber components, including the energy transparent window and/or electrode, and a substrate positioned in the chamber for processing.

5 In one aspect, the invention provides a dielectric, ceramic or semiconductive window having a first plate and a second plate, which when bonded or otherwise secured together form an internal fluid channel or passageway 64 through which a cooling (or heating) fluid can be flowed to provide temperature control of the window. The invention will be described below initially with reference to embodiments having an energy transparent window. Although it
10 should be understood that the description applies to chamber configurations which comprise an electrode. An external control system preferably regulates the temperature of the fluid and adjusts the window or electrode temperature according to system and process requirements. In one aspect, a retaining ring mounts the window or electrode and provides fluid flow through a feedthrough and into the channel or passageway.

15 The invention will first be described in detail below with reference to an inductively coupled plasma chamber having a generally flat lid. A capacitively coupled chamber configuration as well as other inductively coupled chamber configurations will then be described. It is to be understood that the invention can be utilized in other chamber configurations requiring temperature control of a dielectric, non-metallic or semiconductive
20 chamber component.

Figure 1 is a cross sectional view of one embodiment of an etch chamber 2 of the present invention having a generally flat lid assembly 8, including an energy transparent window 48. The chamber 2 generally includes an annular sidewall 4, a bottom wall 6, and a lid assembly 8. A pedestal 18 operating as a cathode is disposed in the lower portion of the
25 chamber and supports a substrate 24 during processing. The pedestal 18 is connected to a cathode power supply 5 which typically biases the pedestal to a negative voltage. A protective edge ring 22 is disposed on the upper surface 20 of the pedestal 18 and defines a perimeter in which a substrate 24 is positioned during processing. A cathode liner 34 may be disposed in the chamber to surround the pedestal 18 and form a sacrificial deposition area which can be
30 easily removed and cleaned. Similarly, an anode liner 32 may be disposed about the interior of the sidewall 4 to provide a removable surface on which deposition can occur during processing

and be easily removed for cleaning. An array 130 of induction coils is disposed above the energy transparent window 48 and will be described in detail below. Excessive process gases and volatile compounds produced during processing are exhausted through a gas outlet 36 by a vacuum pump (not shown). The chamber also includes a slit opening 26 through which
5 substrates enter and exit the processing chamber.

A first RF power supply 132 supplies electrical power through a first impedance matching network 131 to an array 130 of induction coils mounted on the dielectric window 48. Each coil 140, 142 in the array 130 is wound around an axis which is parallel to the chamber axis, i.e., perpendicular to the chamber lid and to the substrate. The RF current through the
10 induction coils produces an RF electromagnetic field in the region of the chamber just below the lid so as to couple RF power to the plasma and thereby enhance the density of the plasma.

Conventionally, a second impedance matching network 133 capacitively couples the second RF power supply 134 to the cathode electrode in pedestal 18 so as to produce a negative DC bias voltage on the cathode electrode relative to the electrically grounded chamber walls. The negative bias voltage on the cathode electrode in pedestal 18 attracts ions from the
15 process gas mixture toward the substrate so that the process gases perform a desired process on the surface of the substrate, such as a conventional process for etching an existing film on the substrate or for depositing a new film on the substrate.

Figures 2-3 depict the wedge shape of each of the eight induction coils 140, 142 in the array 130, the coils being equally spaced around the azimuth of the chamber lid 8. As shown in Figures 2 and 3, each coil 140, 142 has a number of turns of copper wire 142 wound around a hollow coil form 150. Each coil form has a wedge-shaped top surface 154 and a U-shaped cross section when viewed from the side. Specifically, each coil form 150 consists of a curved, rectangular, wide outer surface 153; an almost triangular, wedge-shaped top surface 154; and a
20 curved, narrow, inner tip surface 155. The azimuthal sides 144 of each coil form are open.

Each coil form 150 is composed of a dielectric material so that the coil windings can touch the form without being electrically shorted out. The eight wedge-shaped coil forms 150 are attached to a single, disc-shaped base 156, preferably made of a high strength plastic. Preferably, each induction coil 140, 142 encircles a magnetic core 152, preferably made of
30 ferrite.

Further description of the array and associated plasma chamber described above can be

had with reference to United States Patent Application No. 09/039,216, entitled "A Distributed Inductive Coupled Plasma Source with Ferrite Core Enhancement" filed on March 14, 1998, which application is incorporated herein by reference. Alternatively, a chamber having a flat, spiral wound coil 11 disposed adjacent the window could also be used. Figure 1a is a cross sectional view of a chamber illustrating one embodiment of a flat, spiral wound coil 11.

The temperature control aspects of the invention will be described in reference to the lid assembly 8 which in the first embodiment, shown in cross section in Figure 1, includes a retaining ring 47, an energy transparent window 48 and one or more feedthroughs 54 which connect the window to the retaining ring and provide fluid flow into and out of the window.

Figure 4 is a cross sectional view of a generally flat window 48 having a top plate 92 and a bottom plate 94 which when sealed together form an internal fluid channel 64. The fluid channel 64 is preferably continuous having one or more inlets/outlets 66 formed in the top plate 92. The fluid channel 64 is formed by milling or otherwise forming grooves 100, 112 in one or both of the plates 92, 94. In the embodiment shown in Figure 2, the channel 64 is partially formed in each of the top and bottom plates so that when the plates are bonded or otherwise sealingly connected together they collectively form the channel 64. In an alternative embodiment, one plate may have the majority or even the entirety of the channel disposed therein and the other plate may act as a sealing backing plate. The grooves 100, 112 forming the channels are preferably rounded at corners 97 and may be a depth of about one-third the thickness of the plate. If the channel is formed entirely in the top plate, and the bottom plate is a planar backing surface, then the thickness of the top plate might be increased and the thickness of the bottom plate decreased so that the relative cross sectional thickness of the plates, subtracting the depth of the channel, is substantially the same. The grooves 100, 112 forming the channel 64 are sized and spaced to cover between about 30-60% of the surface area of the window 48. However, the size and spacing of the grooves forming the channel are determined by the application and the desired temperature control parameters useful for a particular processing application.

The lower surface 114 of the bottom plate 94 may include a textured portion having a series of peaks 116 and valleys 118 to increase the surface area of the bottom plate disposed in the chamber, thereby providing additional area on which etched material can deposit. It is believed that increasing the surface of the window adjacent the reaction zone reduces the

likelihood that material will build-up and potentially flake off and thereby reduces the likelihood of contamination of substrates being processed.

The top plate 92 and bottom plate 94 are joined along a bond line 96. The bond line preferably seals the periphery of the window and the area between the grooves 100, 112 to define a sealed flow passageway throughout the window with substantially no leakage between the plates. The method of bonding the plates will vary depending on the materials selected to form the plates. Liquid and/or gaseous fluids are flowed through the passageway to provide temperature control to the window. The fluid is preferably a liquid such as de-ionized water and/or ethylene glycol. Other fluids, such as liquid or gaseous nitrogen or freon, can also be used. Where required in the case of conductive or semiconductive windows, the fluid can be a dielectric fluid. Alternatively, the window could be uniformly heated using heated fluids.

Figures 5 and 6 are a bottom and top view of top and bottom plates 92, 94, respectively. The groove 100 is formed in the lower surface of the top plate 92 and extends from an inlet/outlet, referred to herein as a feedthrough pocket 66, located at the perimeter of the window 48 inwardly toward the center of the window 48. The feedthrough pocket 66 has a first and second diameter which define a pocket shoulder 76 therebetween on which an o-ring can be compressed to form a seal between the retaining ring, the feedthrough pocket 66 of the window and the feedthrough, the latter two will be described in more detail below. The feedthrough pockets are preferably symmetrically arranged about the window for ease in alignment with the retaining ring and the window and to provide uniform flow of fluids into and out of the window. The groove 100 then forms a semicircular pattern as the groove extends outwardly to another inlet/outlet corresponding to a second feedthrough pocket 66 disposed on the outer perimeter of the window 48. Similarly, a groove 112 is formed in the upper surface of the bottom plate 94 and is adapted to mate with the channel 100 of the top plate when the plates are sealed together. The outer perimeter of the bottom plate 94 includes a shoulder 88 which assists in aligning the window in the inner diameter of the chamber and supporting the window on the chamber sidewall 4.

The window 48 is preferably made of materials that are transparent or translucent to electromagnetic radiation, such as RF energy, including alumina (aluminum oxide), aluminum nitride, silicon carbide, silicon, polysilicon, and other dielectric, non-metallic and semiconductive materials and combinations thereof. The plates may be made of the same or

different materials. In addition, materials having a high thermal conductivity can be used to advantage to conduct heat into the fluid in the fluid channel. The window material may include a glazing material that exhibits an increased strength by aligning the material along its natural axis at a bond line.

Figure 7 is a bottom view of a top plate illustrating another pattern for the channel. A variety of other patterns could be formed in the bottom plate as well as the top plate to form a channel having a desired thermal profile across its surface. In addition, multiple channels could be formed in the window having separate inlets and outlets to enable independent temperature control of multiple zones or areas on the window. For example, the central portion of the window may require more heat dissipation as opposed to the peripheral portion of the window. In other embodiments, a different pattern (arcuate, meandering, random or combinations thereof) could be made in the bottom plate and the top plate to achieve different flow patterns and different temperature controlled areas of the lid. Still further, the channels might be asymmetrical, such as with different depths or thickness in different portions of the plate(s), to achieve different thermal conduction conditions in select areas. Still further, the feedthrough and corresponding retainer feedthrough hole can be used for the inlet and another feedthrough and corresponding retainer feedthrough hole for the outlet. In addition, a variety of inlets and outlets may be used to supply fluid to the temperature controlled window. For example, an outlet may be disposed in the window that bypasses the retainer.

Alternatively, window 48 could be of a one-piece construction in which fluid passageways or pathways are drilled or otherwise formed laterally therethrough, and which may be intersecting, parallel or otherwise non-intersecting. However, it would be substantially more difficult, as compared to the above-described two-piece construction, to form such passageways laterally in a one-piece window; to form meandering or other non-straight or curved passageways therethrough; and to handle the greater multiplicities of fluid input and output connectors for the resulting greater number of fluid inputs and outputs that would be required by straighter passageway geometries.

Figure 8 is a partial cross sectional view illustrating the connection between the retaining ring 47 and the window 48 through a feedthrough 54. The retaining ring 47 supports the window 48 in the chamber and provides inlet/outlet connections to the channel 64 in the window 48. The retaining ring 47 includes one or more fluid inlets/outlets 50 to which fluid

connectors 51 are connected. A transverse fluid inlet/outlet channel 41 is formed in the retaining ring between the inlets/outlets 50 and feedthrough channels 57 through which a feedthrough 54 is sealably disposed. The fluid inlets/outlets 50 are generally threaded to allow connection of the fluid inlet/outlet connectors which in turn may be connected to hoses, pipes or other conduits (not shown). The feedthrough channels 57 have an upper portion 59 and a lower portion 61 of varying diameter which define a shoulder 82. The transverse fluid inlet/outlet channel 41 intersects the feedthrough channel 57. The retaining ring 47 includes one or more alignment shoulders 77 which correspond to each feedthrough channel 57 and provide alignment between the retaining ring 47 and the window 48.

The feedthroughs 54 preferably include an elongated body portion having a first and second diameter corresponding to the first and second diameters of the feedthrough channels 57. The lower end of the feedthroughs 54 include an enlarged tapered engagement portion 68. The upper end of the feedthroughs include a threaded portion on which a retaining nut can be received. The feedthroughs define an outer annular channel 55 in which one or more, preferably two, transverse feedthrough ports 60 are formed. The channels 55 and feedthrough ports 60 are in fluid communication with the transverse fluid inlet/outlet channels 41 formed in the retaining ring and a channel formed at least partially along the length of the feedthroughs 54.

The tapered engagement portion 68 of the feedthrough is adapted to fit into the feedthrough pocket 66 of the window 48. The feedthroughs 54 are inserted into feedthrough channels 57 in the retaining ring 47 and secure the window to the retaining ring via the threaded end of the feedthrough and a fastener 56. A sealing element 72 is disposed below the pocket shoulder 76 to seal the tapered portion 68 of the feedthrough in the pocket between the alignment shoulder 77 of the retaining ring 47, the pocket shoulder 76 and the tapered portion 68 of the feedthrough. The pocket alignment shoulder 77 presses the sealing element into position along the tapered engagement portion of the feedthrough 54. Alternatively, the pocket alignment shoulder could simply be a washer that similarly presses the sealing element into position along the tapered portion. A chamber support 86, connected to the upper surfaces of the side wall 42, is located below the lid 48 and supports the lid in position while the fastener 56 is tightened to the feedthrough. Additionally, the sidewall 42 may include a sealing groove 84 into which another sealing element may be placed. This sealing element may be

particularly useful as the chamber is brought to a vacuum and pulls the lid down into engagement with the chamber. A lid support shoulder 88, formed in the lid 48, may assist the lid alignment with the sidewall 42.

A sealing element 80 is located at the top end of the feedthrough 54 to seal the feedthrough and the retaining ring 47. The sealing element(s) may be an O-ring, gasket, sealing compound such as silicone, or other typical sealing elements. To compress the sealing element between the feedthrough and retainer, the fastener 56 includes a tapered fastener portion 78. The tapered portion allows progressive compression of the sealing element against the feedthrough and retainer as the fastener is tightened to the feedthrough. The fastener taper angle may vary between about 0 and about 90 degrees, and in one embodiment, the angle is about 35 degrees from the longitudinal axis of the feedthrough. The resilient sealing element(s) allows for misalignment and for thermal expansion and contraction between the feedthrough and the lid and between the feedthrough and the retainer.

Two other embodiments of a chamber and window are illustrated in Figures 9 and 10. The embodiments shown illustrate two respective configurations for an inductively coupled plasma chamber. In Figure 9, a substrate 120 is supported on a pedestal 122 operating as a cathode electrode and including an electrostatic chuck and a protective edge ring 124.

The RF biased pedestal 122 acts as a cathode in opposition to the grounded silicon window 152. The first RF power supply 134 supplies bias power to the pedestal electrode 122.

A lower gas feed 144 penetrates the silicon ring 128 and supplies gas mixture from several gas sources 196 through a bank of mass flow controllers 148 to a processing region 150 over the pedestal 122.

A window 152 made of silicon, polysilicon or other semiconductive material, is disposed in opposition to the pedestal 122. Its thickness and semiconductor doping level are chosen so that it both can act as an electrode, here as an electrically grounded anode, as well as can pass generally axial RF magnetic fields generated by inner and outer inductive coils 154, 156 positioned behind the window 152. A cooling channel 94 is formed in the window 152 to provide temperature control of the window similar to the embodiments described above. The cooling channel 94 can replace the thermal control plate 157 which is typically coupled to the back of window 152 and below the coils 154, 156. The inner and outer coils 154, 156 are powered respectively by second and third RF power supplies 158, 160. The RF power supplies

158, 160 are connected to respective first ends of the coils 154, 156 and tuning and loading capacitors 162 are connected between the first and second ends of the coils 154, 156 and ground. The RF power supplied to the coils 158, 160 in such proportions as to provide a more uniform plasma is inductively coupled into the source region of the processing space 150
5 between the pedestal 122 and the window. The amount of power is primarily responsible for the density or strength of the plasma. The power supplied to the pedestal 122 is capacitively coupled into the plasma adjacent to the principal surface of the wafer 120 and is responsible for the amount of DC bias of the plasma relative to the wafer.

10 An annular pumping channel 170 surrounds the processing region 150 and is connected to it through an annular flow constriction 172.

Figure 10 illustrates another ICP type chamber having a domed window with cooling channel 94 formed therein. The chamber components are similar to those of Figure 9 and are numbered accordingly. As can be seen from the Figure, this embodiment includes a domed shape window having an inductive coil disposed around the perimeter of the dome. The cooling channels 94 of the invention are provided in the dome to enable direct temperature control of the dome.
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In another embodiment illustrated in Figure 11, the invention provides a parallel plate type reactor which typically includes an upper and a lower electrode. The lower electrode 258 is a substrate support member. In such an embodiment, the construction provides for direct temperature control of the upper electrode. The upper electrode generally comprises a backing plate 280 supporting a facing plate 212 having a substantially uniform thickness thereacross. The facing plate provides an electrode surface which is exposed to a plasma in the chamber and is therefore preferably made of a material which is compatible with the plasma chemistry used in the particular process. These materials may include graphite, polycrystalline silicon, quartz,
20 glassy carbon, single crystal silicon, pyrolytic graphite, silicon carbide, alumina, zirconium, diamond coated materials or titanium oxide.
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A support frame 214 in the shape of an annular ring is bonded or otherwise connected to the upper surface of the electrode plate 212. The support frame 214 provides mechanical support for the electrode plate and also provides electrical and thermal connection of the electrode plate 212 to an RF source and heat sink. Thus, the support frame is preferably made
30 of a material having a high electrical and thermal conductivity, such as graphite, aluminum,

copper, stainless steel and the like. In one aspect, the support frame is an annular ring which is disposed at least partially on the outer perimeter of the electrode plate.

The electrode plate 212 is supported in the chamber on the support frame 214. A backing plate 280 is connected to the upper surface of the electrode plate. A pair of baffle plates 287, 288 are preferably disposed between the backing plate and the electrode plate to uniformly distribute gases introduced to the back of the baffle plates. The gases enter the chamber through one or more apertures 216 formed in the electrode plate 212. The support frame 214 is supported on one or more insulating rings 290, 292 disposed on the chamber wall.

A cooling assembly of the invention is provided to deliver a cooling fluid to the electrode plate 212. Channels 64 are formed in the electrode plate 212 and are connected to a source of fluid by one or more feedthroughs 54 disposed through the support frame 214 and backing plate 280. The backing plate 280 and support frame 214 provide a channel in which the feedthrough is disposed to connect to the electrode plate 212 to deliver fluid thereto. The connection to the electrode plate 212 can be formed as shown in the embodiment of Figures 1 and 4-8 described above. The plate 212 is formed of two facing members which may be made of the same or different materials similarly to the embodiments described above. In addition, the channels 64 may be formed in both plates or substantially in one plate with a generally smooth surface of the other plate forming a wall of the channels. In addition, the top plate may be a metal or conductive material while the bottom plate is a silicon containing material. In a preferred embodiment, both plates are formed of a silicon containing material. Both plates could be a metal or other conductive material.

Alternatively, the baffle plates could be omitted and the gases could enter the chamber via orifices mounted adjacent to or within the chamber sidewalls. The facing plate 212 may be made thicker or stronger and thus obviating the need for a backing plate to 280. In such a case, the electrode plates would simply be of two-piece construction with the cooling channels defined therebetween as described above, for example, in connection with Figure 1, but with no overhead coil and with at least the plate facing the plasma being a conductor or semi-conductor. Both plates of such a two-piece electrode plate assembly could also be made of metal, *e.g.*, anodized aluminum or the surface facing the plasma could be coated with a material to help preclude deterioration under plasma conditions or to enhance compatibility with the plasma process. Also, alternatively the electrode plates could be of a one-piece

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Claims:

- 1 1. A processing chamber, comprising:
 - 2 a) a chamber body having a substrate support member disposed therein;
 - 3 b) a chamber cover, comprising:
 - 4 i) a retaining ring; and
 - 5 ii) a lid, comprising:
 - 6 a) a first plate and a second plate sealably connected together and
 - 7 defining a fluid channel at least partially therebetween; and
 - 8 b) a fluid inlet and outlet fluidly connected to the fluid channel.
- 1 2. The processing chamber of claim 1, wherein the lid is connected to the retaining ring by
- 2 one or more feedthroughs.
- 1 3. The processing chamber of claim 2, wherein the one or more feedthroughs enable fluid
- 2 flow into and out of the fluid inlet and fluid outlet.
- 1 4. The substrate processing system of claim 1, wherein the lid further comprises one or
- 2 more feedthrough pockets in which the one or more feedthroughs are received to connect the
- 3 lid to the retaining ring.
- 1 5. The substrate processing system of claim 4, wherein the one or more feedthroughs
- 2 comprise an enlarged engagement portion insertable into the one or more feedthrough pockets.
- 1 6. The substrate processing system of claim 5, wherein the one or more feedthrough
- 2 pockets comprise a pocket shoulder to receive a sealing element therein.
- 1 7. The substrate processing system of claim 6, further comprising a fastener adapted to
- 2 attach the feedthrough to the retaining ring.
- 1 8. The substrate processing system of claim 7, wherein the retaining ring defines one or

2 more fluid passages and one or more feedthrough channels fluidly connected to the fluid
3 passages.

1 9. The substrate processing system of claim 4, wherein the feedthrough comprises a
2 channel along its length and one or more ports connected to the channel.

1 10. The substrate processing system of claim 8, wherein the retaining ring comprises a
2 pocket alignment shoulder adapted to align the lid to the retaining ring.

1 11. The substrate processing system of claim 1, wherein the first and second plates each
2 comprise a portion of the fluid channel.

1 12. The substrate processing system of claim 11, wherein the fluid channel is continuous
2 between the inlet and the outlet.

1 13. The substrate processing system of claim 12, further comprising a feedthrough pocket
2 fluidly connected to the lid passageway and adapted to connect to a feedthrough to secure the
3 lid to the retaining ring.

1 14. The substrate processing system of claim 13, wherein the passageway forms a
2 circuitous pattern substantially throughout the lid.

1 15. The substrate processing system of claim 14, wherein the passageway surface area
2 comprises at least about 35% of the surface area of the lid.

1 16. The substrate processing system of claim 15, wherein the lid is an energy transparent
2 window or an electrode.

1 17. The substrate processing system of claim 16, wherein the energy transparent window or
2 electrode are made of a material selected from the group comprising aluminum oxide,
3 aluminum nitride, silicon carbide, silicon, polysilicon and combinations thereof.

1 18. A temperature controllable lid for a processing system, comprising:

- 2 a) a first plate sealably connected to a second plate;
3 b) at least one channel formed between the first and second plates; and
4 c) one or more inlets and one or more outlets connected to the channel.

1 19. The lid of claim 18 wherein the first and second plates each comprise a portion of the
2 temperature control passageway.

1 20. The lid of claim 18, wherein the temperature control passageway is continuous between
2 an inlet and outlet.

1 21. The lid of claim 18, wherein the passageway is disposed over about 35% of the surface
2 area of the lid.

1 22. The lid of claim 18, wherein the lid comprises at least one feedthrough pocket in fluid
2 communication with the passageway and a feedthrough disposed in the feedthrough pocket.

1 23. The lid of claim 22, wherein the feedthrough pocket comprises a pocket shoulder and a
2 sealing element circumferentially disposed around the feedthrough in proximity to the pocket
3 shoulder.

1 24. The lid of claim 23, wherein the feedthrough comprises an enlarged engagement
2 portion adapted to be inserted into the feedthrough pocket.

1 25. The lid of claim 24 wherein the plates define two or more channels, each channel
2 connected to at least one inlet and one outlet.

1 26. The lid of claim 18 wherein the plates are comprised of a material selected from the
2 group comprising aluminum oxide, aluminum nitride, silicon carbide, silicon, polysilicon and
3 combinations thereof.

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4 carbide, alumina, zirconium, diamond coated materials, titanium oxide or combinations
5 thereof.

1 35. An electrode assembly for use in a wall of a processing chamber, comprising:
2 an electrode having a substantially uniform thickness and defining one or more fluid
3 channels at least partially therethrough; and
4 a support frame connected at least partially to one surface of the electrode.

1 36. The electrode assembly of claim 35 wherein the electrode is comprised of a plate and
2 the plate defines one or more apertures therethrough.

1 37. The electrode assembly of claim 36 further comprising a backing plate supporting the
2 electrode.

1 38. The electrode assembly of claim 35 wherein the electrode is comprised of a material
2 selected from the group consisting of graphite, polycrystalline silicon, quartz, glassy carbon,
3 single crystal silicon, pyrolytic graphite, silicon carbide, alumina, zirconium, diamond coated
4 materials, titanium oxide or combinations thereof.

1 39. The electrode assembly of claim 35 wherein the electrode is comprised of a metal.

1 40. The electrode assembly of claim 35 wherein the electrode comprises a coating of
2 graphite, polycrystalline silicon, quartz, glassy carbon, single crystal silicon, pyrolytic graphite,
3 silicon carbide, alumina, zirconium, diamond coated materials, titanium oxide or combinations
4 thereof formed thereon.

1 41. A plasma chamber for processing a workpiece, comprising:
2 a workpiece support; and
3 a chamber cover facing said workpiece support, the chamber cover comprising:
4 a first plate;
5 a second plate sealably engaged with the first plate; and

6 at least one fluid channel defined within said chamber cover and defining one or
7 more fluid pathways distributed generally over the area of the chamber cover.

1 42. The plasma chamber of claim 41 wherein the fluid channel is disposed at least partially
2 between the first and second plates.

1 43. The plasma chamber of claim 42 wherein the channel is partially formed between the
2 first and second plates.

1 44. The plasma chamber of claim 42 wherein the channel is defined by a groove in one of
2 the plates and the generally smooth opposing face of the other plate.

1 45. The plasma chamber of claim 42 wherein the channel is defined by grooves formed in
2 both the first and second plates.

1 46. The plasma chamber of claim 41 wherein the one or more fluid pathways are arcuate,
2 radial, meandering or combinations thereof.

1 47. The plasma chamber of claim 41 wherein the chamber cover is comprised of a
2 dielectric material, a conductive material, a semiconductive material, or combinations thereof.

1 48. The plasma chamber of claim 41 wherein one plate is comprised of one material and
2 the other plate is comprised of another material.

1 49. The plasma chamber of claim 47 wherein the plate facing the workpiece support is
2 comprised of a silicon containing material.

1 50. The plasma chamber of claim 47 wherein at least one plate is comprised of a metal or
2 alloy thereof.

1 52. The plasma chamber of claim 41 wherein the chamber cover comprises a conductive or
2 semiconductive electrode.

1 53. The plasma chamber of claim 41 wherein the chamber cover is dielectric or
2 semiconductive and is transmissive to RF energy.

1 54. The plasma chamber of claim 41 wherein the chamber cover comprises a window
2 transmissive to RF energy, and which further comprises an antenna disposed adjacent to the
3 chamber cover to couple RF energy through the window and into the chamber.

1 55. The plasma chamber of claim 54 wherein the window is an electrode.

1 56. The plasma chamber of claim 52 wherein a dielectric fluid is circulated through the
2 fluid channel.

1 57. A plasma processing chamber, comprising:
2 a substrate support;
3 an antenna to inductively couple RF energy into the chamber to energize one or more
4 processing gases within the chamber into a plasma; and
5 a window comprising a wall of the chamber between the antenna and the substrate
6 support, the window being transmissive to RF energy radiated by the antenna into the chamber
7 and defining one or more interior fluid channels disposed generally throughout the window and
8 capable of supporting a fluid flow therethrough.

1 58. The plasma chamber of claim 57 wherein the window comprises facing first and second
2 members, at least one of the facing members defining a groove therein comprising at least a
3 portion of the interior fluid channel, the facing members being sealingly engaged with each
4 other.

1 59. The plasma chamber of claim 58 wherein the fluid channel is disposed at least partially
2 between the facing members.

1 60. The plasma chamber of claim 58 wherein the other of the facing members defines a
2 generally smooth surface which in conjunction with the groove defines the channel.

1 61. The plasma chamber of claim 57 wherein the channel follows a circuitous path.

1 62. The plasma chamber of claim 57 wherein one or more of the fluid channels are
2 distributed generally throughout the area of the window.

1 63. The plasma chamber of claim 57 wherein the window is comprised of a dielectric or
2 semiconductive material.

1 64. The plasma chamber of claim 63 wherein at least one of the members is comprised of a
2 silicon containing material.

1 65. The plasma chamber of claim 64 wherein at least one of the members is comprised of
2 silicon.

1 66. The plasma chamber of claim 64 wherein at least one of the members is comprised of
2 silicon carbide.

1 67. The plasma chamber of claim 57 wherein the window is comprised of aluminum oxide
2 or silicon nitride.

1 68. The plasma chamber of claim 57 wherein the window is comprised of at least one of
2 silicon or silicon nitride.

1 69. The plasma chamber of claim 57 wherein dielectric fluid is flowed through the

2 channel.

1 70. The plasma chamber of claim 57 wherein the window comprises an electrode.

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ABSTRACT OF THE DISCLOSURE

The present invention provides a temperature controlled energy transparent window or electrode used to advantage in a substrate processing system. The invention also provides methods associated with controlling lid temperature during processing and for controlling etching processes. In a preferred embodiment, the invention provides a fluid supply system for the lid which allows the fluid to flow through a feedthrough and into and out of a channel formed in the window or electrode. The fluid supply system may also mount the window or electrode to a retaining ring which secures the window or electrode to the chamber. In another aspect, the invention provides a bonded window or electrode having a first and second plate having a channel formed in the plates so that when the plates are bonded together they form a channel therein through which a temperature controlling fluid can be flowed. An external control system preferably regulates the temperature of the fluid.

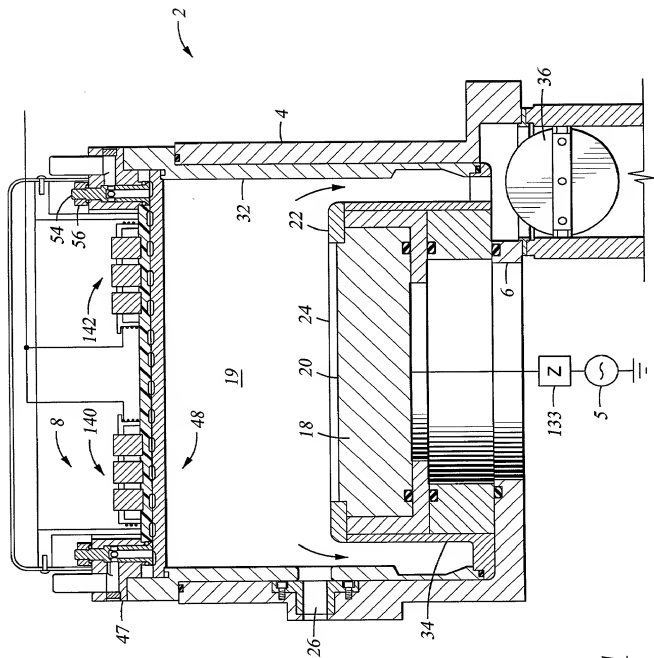


Fig. 1

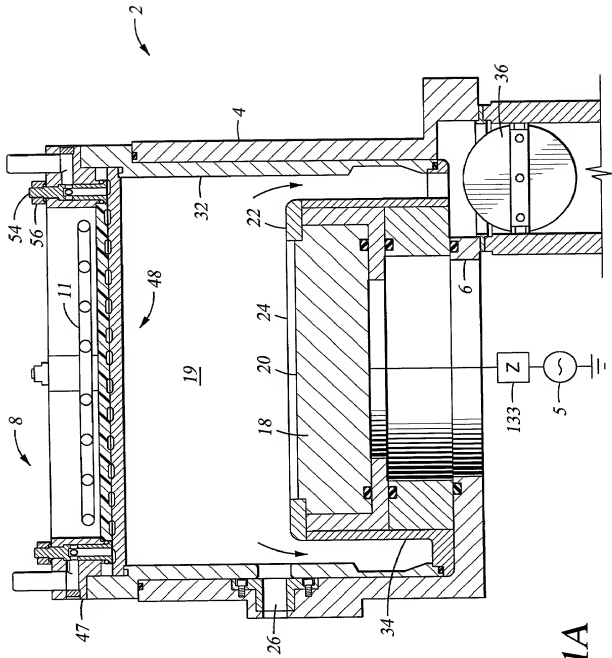
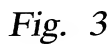
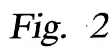


Fig. 1A



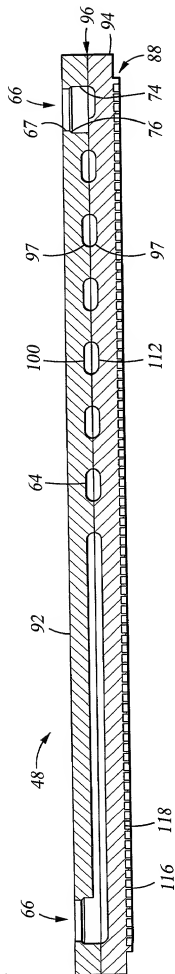


Fig. 4

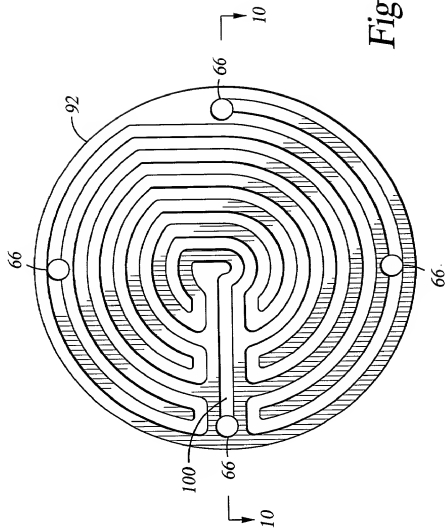


Fig. 5

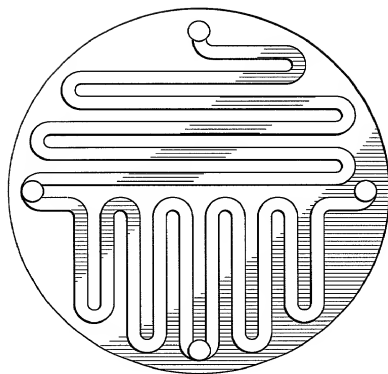


Fig. 7

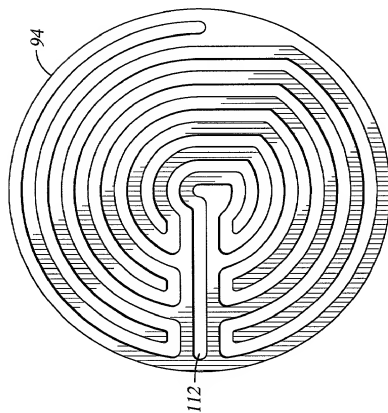
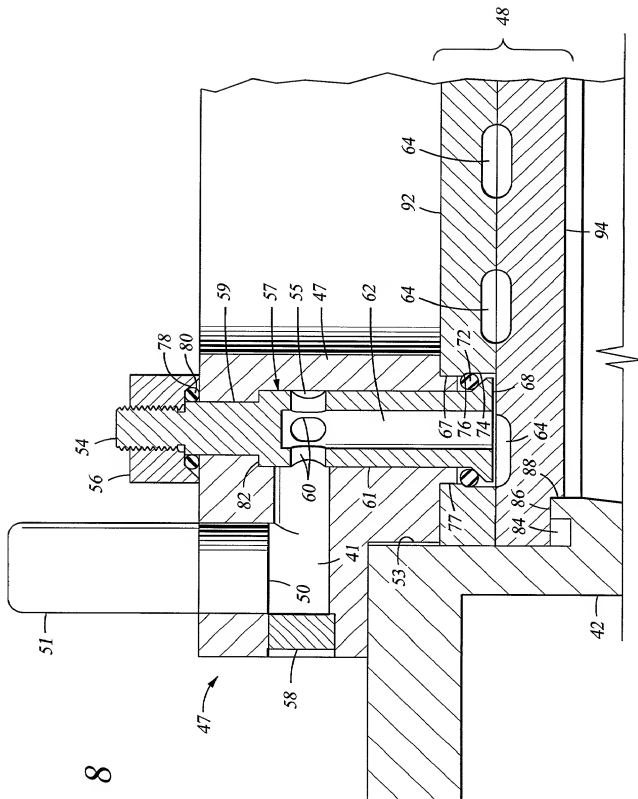


Fig. 6

Fig. 8



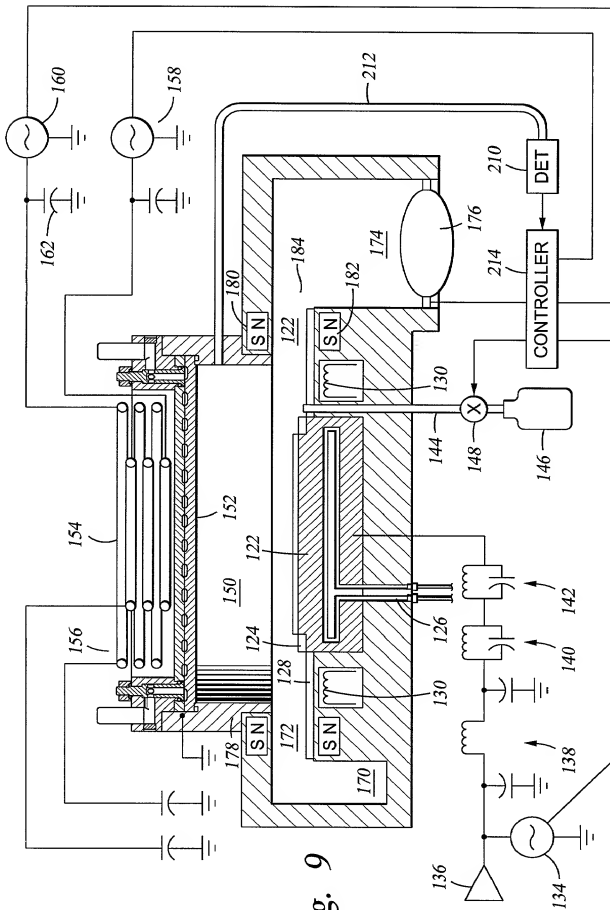


Fig. 9

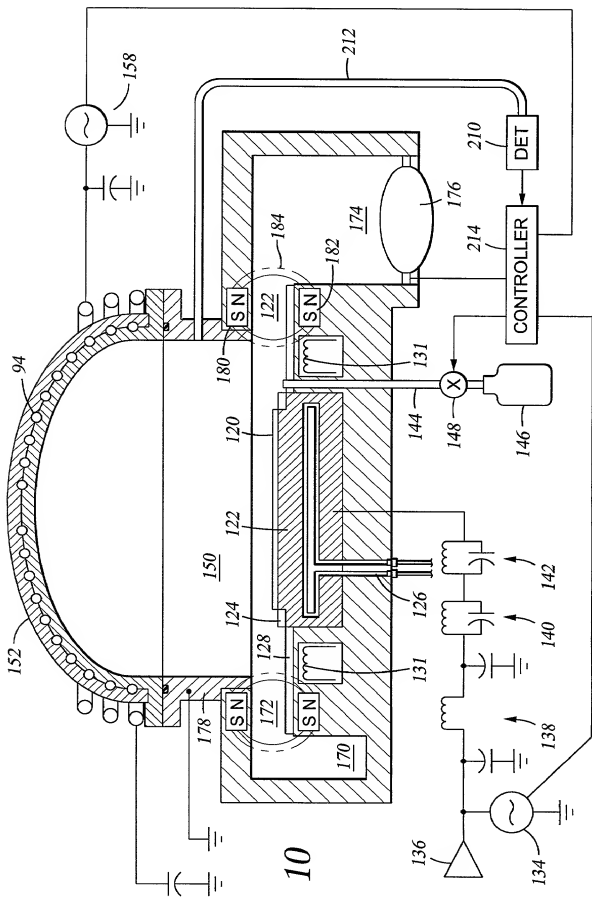


Fig. 10

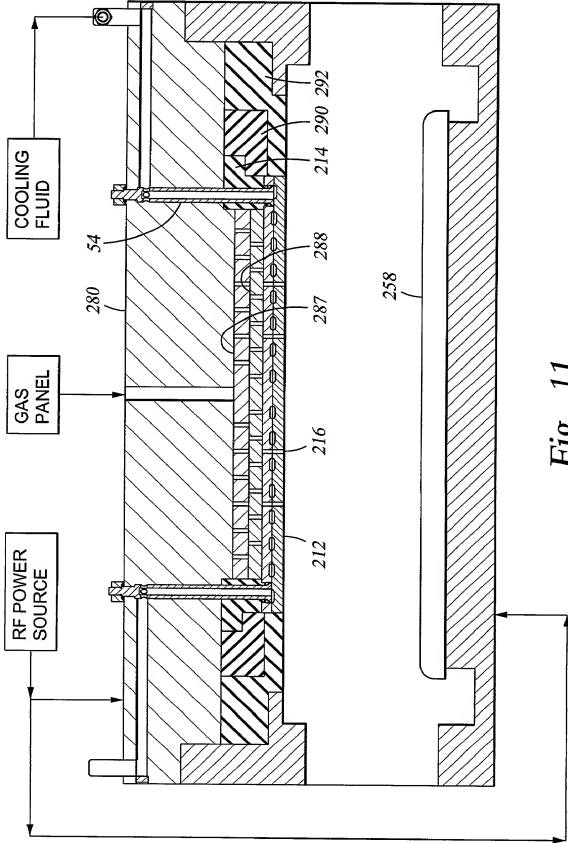


Fig. 11